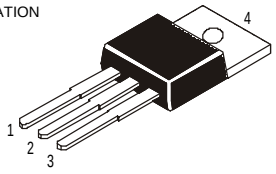
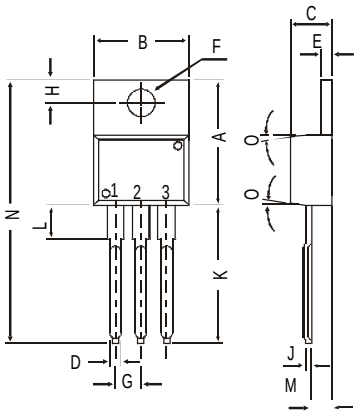
TO-220 Plastic Package **CSA940, CSC2073**

CSA940 PNP PLASTIC POWER TRANSISTOR
CSC2073 NPN PLASTIC POWER TRANSISTOR

Power Amplifier Applications and Vertical Output Applications

PIN CONFIGURATION
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR





All diminsions in mm.

DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
O	DEG 7	

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	*max.*	*150 V*
Collector-emitter voltage (open base)	V_{CEO}	*max.*	*150 V*
Collector current	I_C	*max.*	*1.5 A*
Total power dissipation up to T_C = 25°C	P_{tot}	*max.*	*25 W*
Junction temperature	T_j	*max.*	*150 °C*
Collector-emitter saturation voltage			
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	*max.*	*1.5 V*
D.C. current gain			
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	*min.*	*40*
		max.	*140*

RATINGS *(at T_A=25°C unless otherwise specified)*

Limiting values			
Collector-base voltage (open emitter)	V_{CBO}	*max.*	*150 V*
Collector-emitter voltage (open base)	V_{CEO}	*max.*	*150 V*
Emitter-base voltage (open collector)	V_{EBO}	*max.*	*5.0 V*

Collector current	I_C	*max.*	*1.5 A*
Base current	I_B	*max.*	*0.5 A*
Total power dissipation up to T_C = 25°C	P_{tot}	*max.*	*25 W*
Total power dissipation up to T_A = 25°C	P_{tot}	*max.*	*1.5 W*
Junction temperature	T_j	*max.*	*150 °C*
Storage temperature	T_{stg}	*–65 to +150*	*°C*

CHARACTERISTICS

T_{amb} = 25°C unless otherwise specified

Collector cutoff current			
I_E = 0; V_{CB} = 120 V	I_{CBO}	*max.*	*10 µA*
Emitter cut-off current			
I_C = 0; V_{EB} = 5 V	I_{EBO}	*max.*	*10 µA*
Breakdown voltages			
I_C = 1 mA; I_B = 0	V_{CEO}	*min.*	*150 V*
I_C = 1 mA; I_E = 0	V_{CBO}	*min.*	*150 V*
I_E = 1 mA; I_C = 0	V_{EBO}	*min.*	*5.0 V*
Saturation voltages			
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	*max.*	*1.5 V*
Base emitter on voltage			
I_C = 500 mA; V_{CE} = 10 V	$V_{BE(on)}$	*min.*	*0.65 V*
		max.	*0.85 V*
D.C. current gain			
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	*min.*	*40*
		max.	*140*
Output capacitance at f = 1 MHz			
I_E = 0; V_{CB} = 10 V ***NPN***	C_o	*typ.*	*35 pF*
PNP		*typ.*	*55 pF*
Transition frequency			
I_C = 500 mA; V_{CE} = 10 V	f_T	*typ.*	*4 MHz*

Customer Notes

Disclaimer

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